Silicon NPN Power Transistors 2SC4880

DESCRIPTION

·With TO-3PFM package
·High breakdown voltage
·High speed switching

APPLICATIONS

·For color TV display horizontal deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

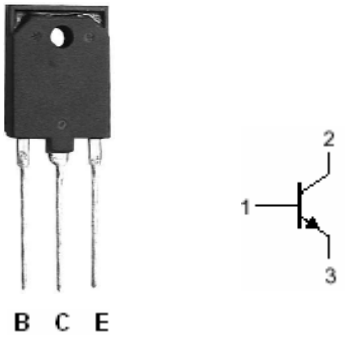

Fig.1 simplified outline (TO-3PFM) and symbol

Absolute maximum ratings(Tc=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1700	V
V_{CEO}	Collector-emitter voltage	Open base	900	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		12	A
P_C	Collector power dissipation	T_C=25□	100	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=10mA; R_{BE}=∞	900			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=1mA; I_C=0	5			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=10A; I_B=2.5 A			5.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=10A; I_B=2.5 A			1.5	V
I_{CES}	Collector cut-off current	V_{CE}=1700V;R_{BE}=0			500	μA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			100	μA
h_{FE}	DC current gain	I_C=1A ; V_{CE}=5V	8		40	

PACKAGE OUTLINE

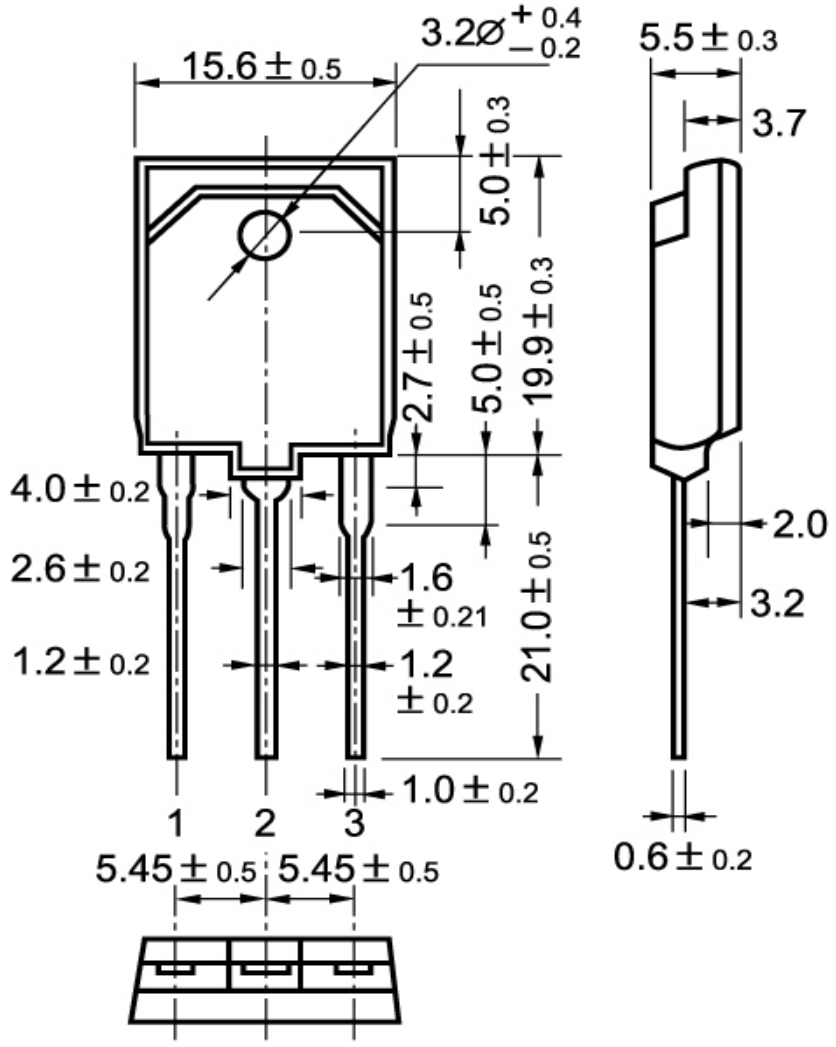

Fig.2 Outline dimensions